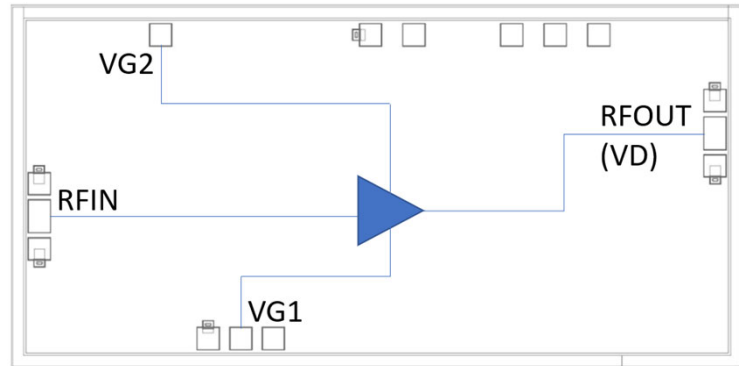


Features

- Frequency: DC-55GHz
- Small Signal Gain: 15 dB
- Gain Flatness: $\leq \pm 1$ dB @ 3-55GHz
- Noise Figure: 3 dB @ 30GHz
- P1dB: 21 dBm @ 30GHz
- Psat = 23.5 dBm @ 30GHz
- Power Supply: +8V/200mA
- Input/Output: 50 Ω
- Die Size: 3.3 x 1.6 x 0.05 mm

Typical Applications

- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

Functional Block Diagram

Electrical Specifications

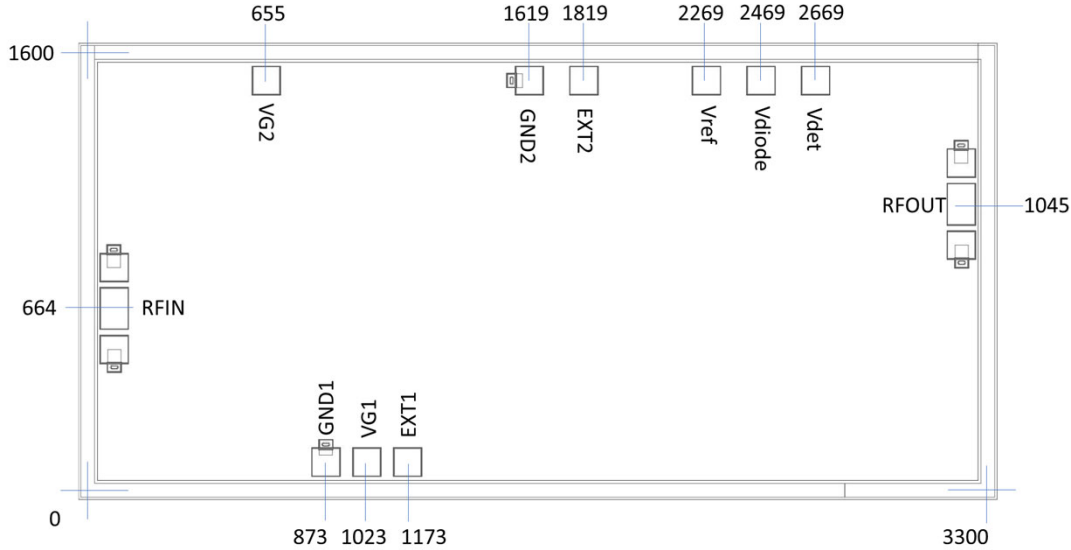
TA = +25°C, VD = +8V, VG1 = -0.4V, VG2 = 3.6V, ID = 200mA

Parameters	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Units
Frequency	DC-4			4-44			44-55			GHz
Small Signal Gain	16	16	19	15	15.5	16	15	15	16	dB
Gain Flatness		± 2			± 0.5			± 0.5		dB
Noise Figure	4	4	5	2.0	3	4	4	5	6	dB
Output 1dB Compression (P1dB)	> 23			> 21			> 17			dBm
Saturated Output Power (Psat)	> 25			> 23.5			> 20.5			dBm
Input Return Loss	< 10									dB
Output Return Loss	< 10									dB

* Adjust VG1, VG2 slightly to obtain device current of 200 mA.



Outline Drawing:
All Dimensions in μm

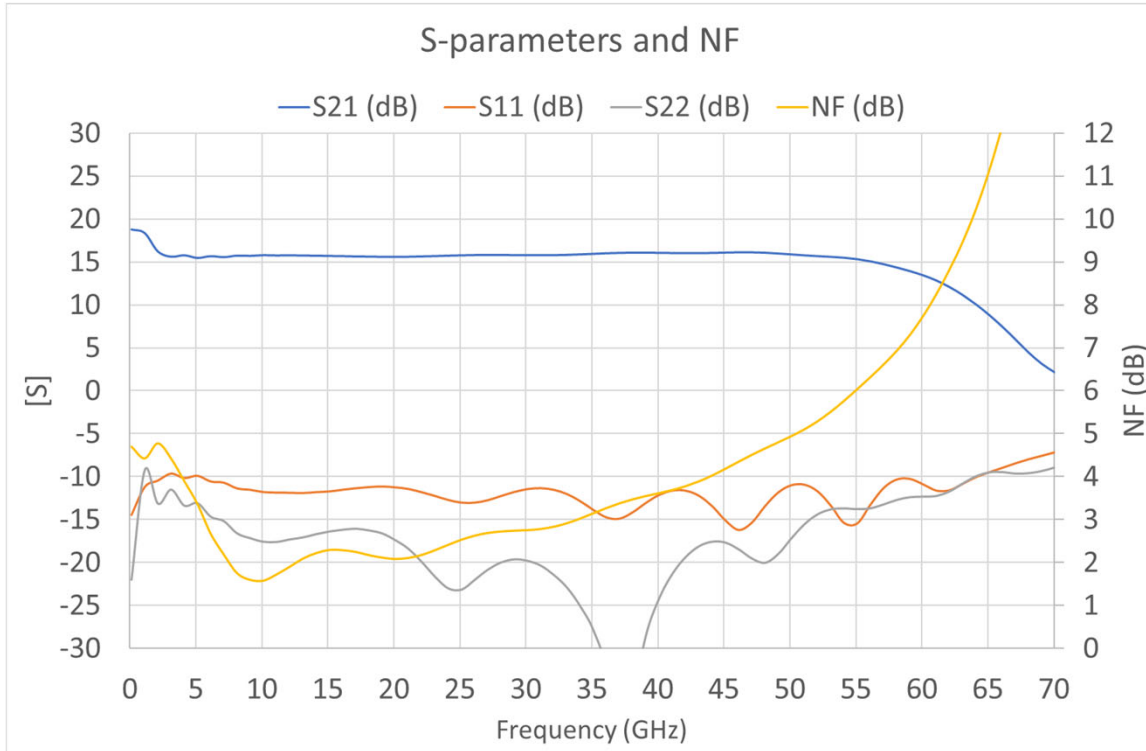


Pad Description

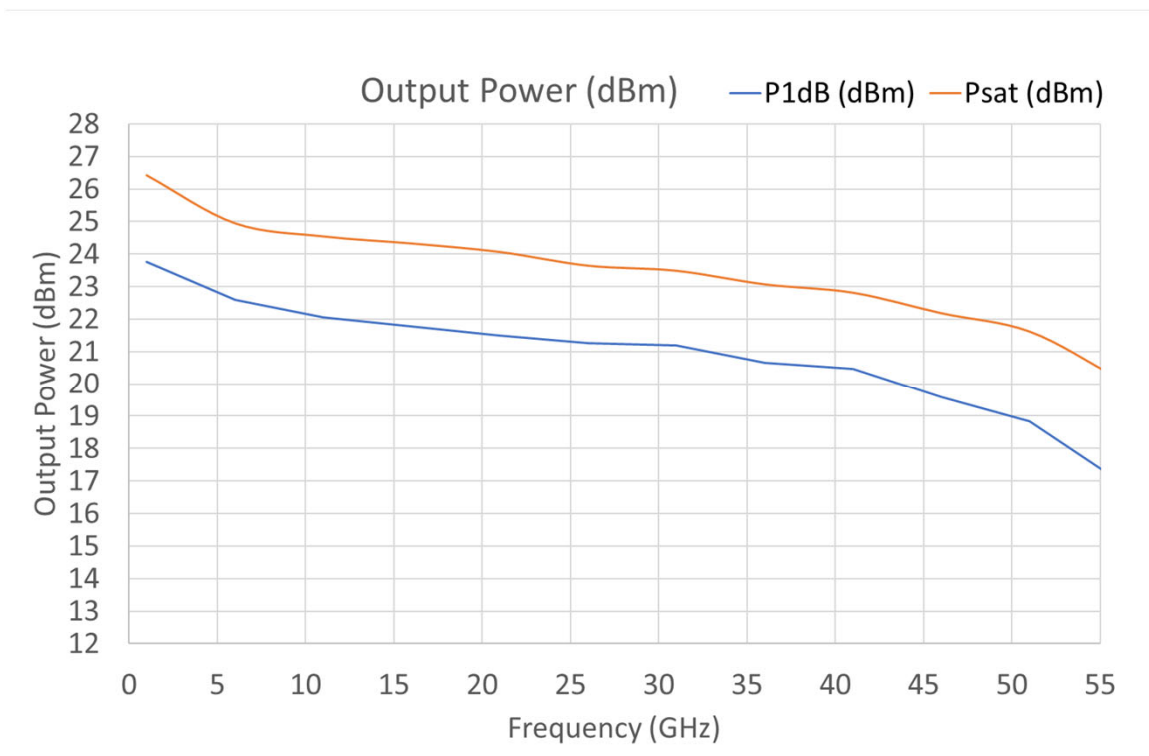
No	Function	Description
1	RF IN	Signal input terminal, connected to 50Ω circuit, DC-coupled
2	RF OUT	Signal output terminal, connected to 50Ω circuit; blocking capacitor required; external DC biasing network required.
3	VG1	Amplifier 1 st gate bias; connect to external 1000pF and 0.01uF bypass capacitors.
4	VG2	Amplifier 2 nd gate bias; connect to external 1000pF and 0.01uF bypass capacitors.
5	EXT1	External bypass pad; connect to external bypass capacitors.
6	EXT2	External bypass pad; connect to external bypass capacitors.
7	Vdiode	Diode biasing voltage
8	Vref	Reference diode output voltage
9	Vdet	Detector output voltage
10	GND1, GND2	Ground pads.



S-parameters and NF

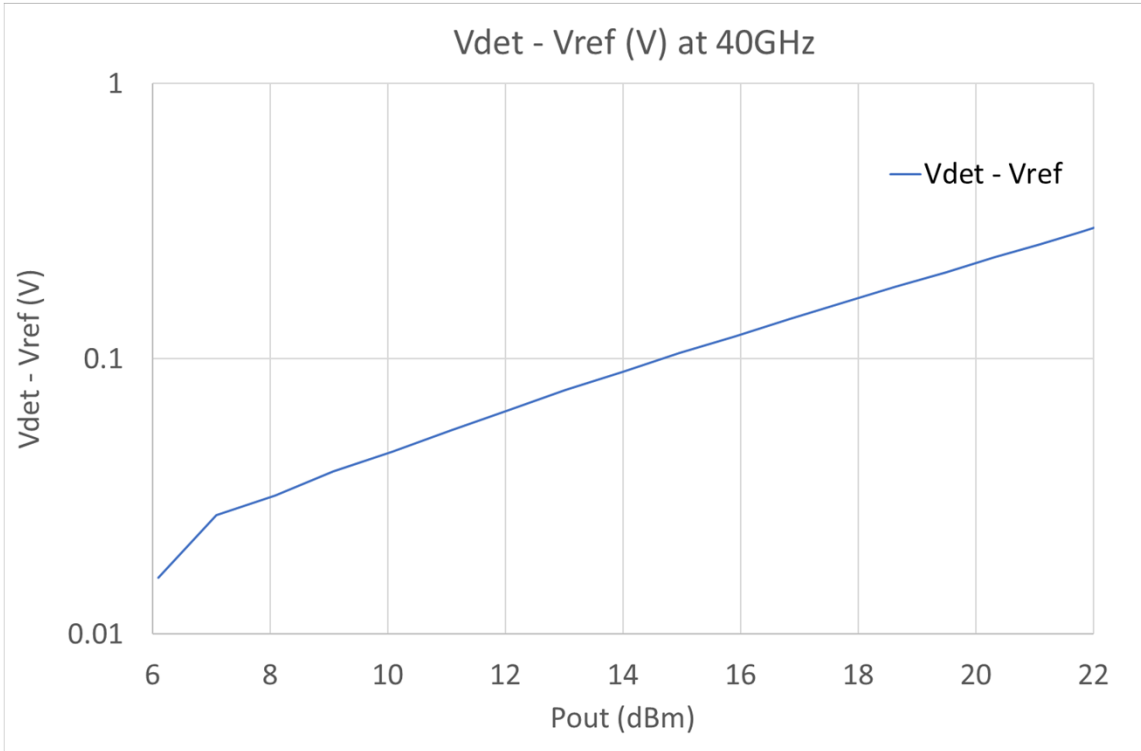


P1dB and Psat

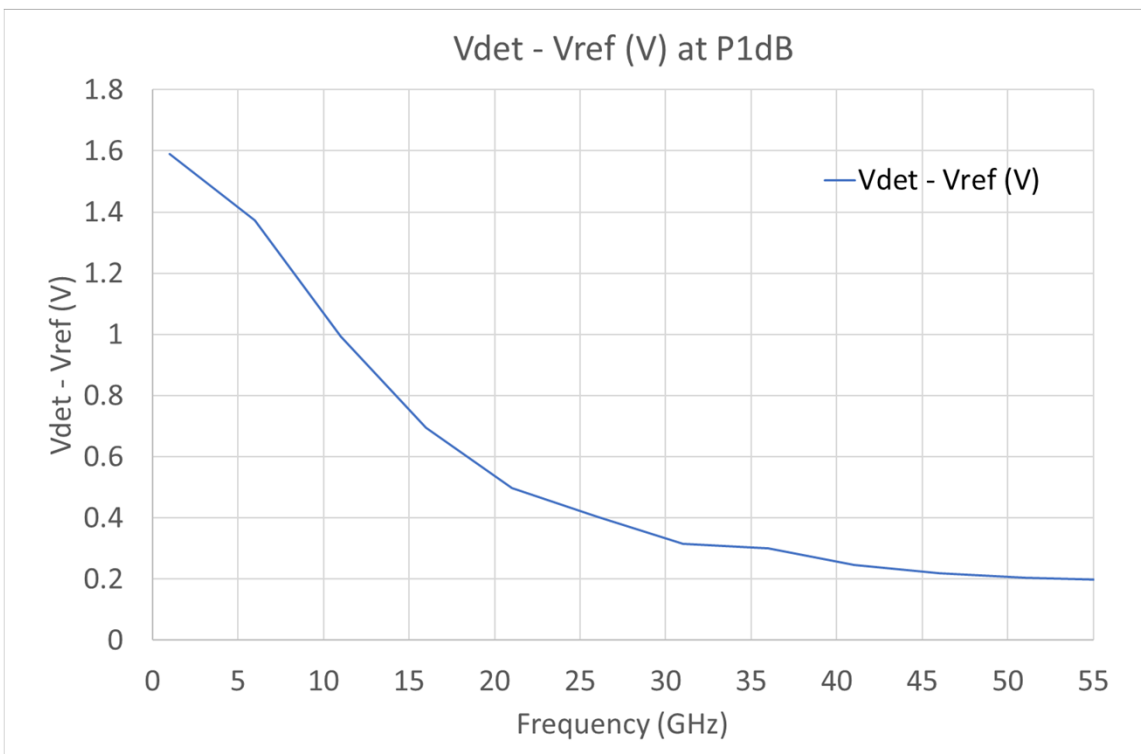




Power Detection: $V_{det} - V_{ref}$ vs P_{out} at 40GHz, $V_{diode} = 1V$

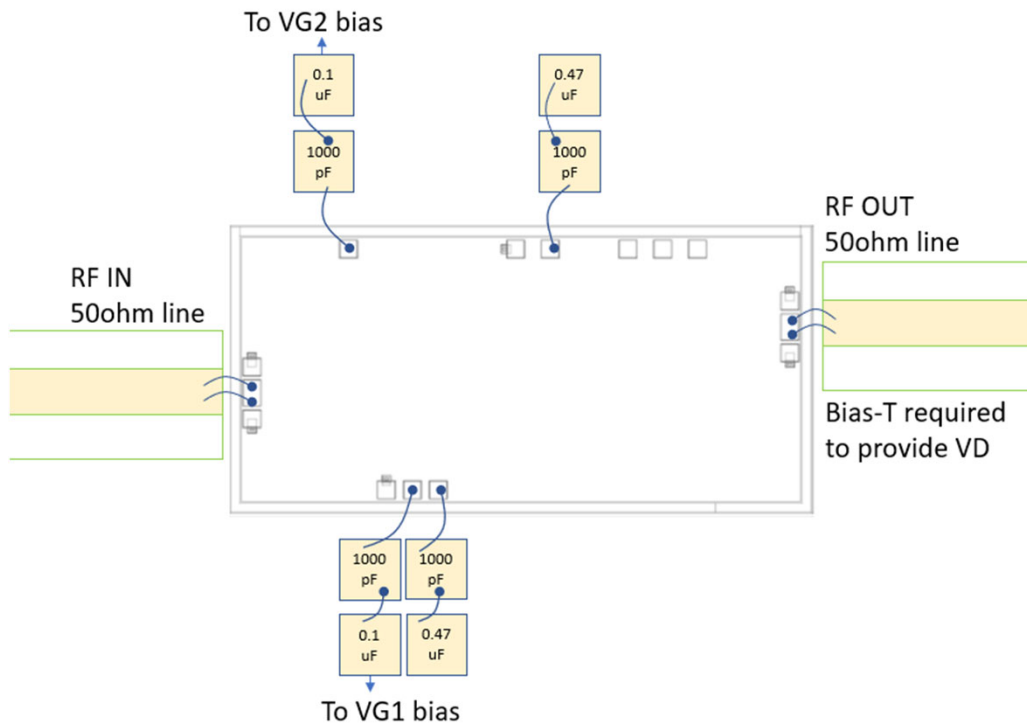


Power Detection: $V_{det} - V_{ref}$ vs Frequency at P1dB, $V_{diode} = 1V$





Assembly Drawing



Notes:

1. Die thickness: 50um
2. DC bond pad is 100 x 100 μm^2
3. RF IN/OUT bond pad is 100 x 160 μm^2
4. Bond pad metalization: Gold
5. Backside metalization: Gold
6. Backside of the die (GND)